

IN THE SPECIFICATION

Please amend the paragraph beginning at page 7, line 3 of the specification as follows:

For this reason, in this embodiment, the back surface 110b is lapped with the lapping device 180. However, the back surface may be lapped by any suitable conventional etching techniques. As shown in FIG. 10, the metallic layer 115 is formed on the lapped back surface 110b of the wafer 110. With respect to the metallic adhesive [[means]] 130 and the temperature in the chip attachment process, it is preferable to use a metal having a low melting point as the metallic layer 115. For example, the metal can be Va (Vanadium), Au (Gold), Ni (Nickel), Ag (Silver), Cu (Copper), Al (Aluminum), Pb (Lead), Sn (Tin), Sb (Stibium), Pd (Palladium) and metal-containing compounds thereof. Of course, the present invention is not limited to such metals and compounds. Those of ordinary skill in the art should also be aware the other suitable metals or metallic compounds are well within the broad scope of the present invention.

Please amend the paragraph beginning at page 7, line 23 of the specification as follows:

Conventionally, a step of removing the photoresist normally follows the washing step. However, with the conventional method, a delamination problem of the semiconductor chip from the adhesive tape occurs. In order to prevent this problem, in accordance with the embodiment of the present invention, as shown in FIG. 12, a chip attachment step (step 194) is followed. Each of the semiconductor chips 112 is separated from the wafer (110 in FIG. 11), and attached to the upper surface 121 of the base substrate 120 by interposing an adhesive 130 having a low melting point such as solder therebetween. Herein, the metallic adhesive 130 is solidified at room temperature, and therefore the curing step for the Ag-epoxy adhesive is omitted. Since a metallic layer 115 is formed on the back surface of the semiconductor chip 112, the metallic adhesive 130 is more firmly attached to the semiconductor chip 112. The metallic adhesive 130 can be provided in various forms such as a ribbon, paste, wire or any other suitable patterns.

Please amend the paragraph beginning at page 8, line 1 of the specification as follows:

If the metallic adhesive 130 is used, the die-attaching step is carried out at higher temperature than if the Ag-epoxy adhesive is used. For example, with the solder, the die attaching step is processed at a temperature of approximately 150oC or more. However, since

the mirrors 116 of the semiconductor chip are coated with the photoresist 113, although the die-attaching step is carried out at a high temperature, the mirrors 116 of the semiconductor chips are not damaged.

Please amend the paragraph beginning at page 9, line 11 of the specification as follows:

When the metal lid frame 152 is attached to the metal sealing ring 124 by thermo-compression, a portion of the metal lid frame 152 attached to the metal sealing ring 124 has a thickness less than the thickness of the other portion of the metal lid frame 152. This allows the effective heat transfer from a thermo-compression means [] through the upper surface of the metal lid frame 152. An adhesive means having a lower melting point than that of the above-described metall_ic adhesive 130 is used between the metal sealing ring 124 and the metal lid frame 152. This prevents the conventional deformation problem that results from re-melting the metall_ic adhesive 130.